Att'y Dkt. No.	M#	Client Ref.
	284032	01F171

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Applicant: YAMADA et al

Appln. No.: 09/993,967

Filing Date: November 27, 2001

Date: February 11, 2002   Page 1 of 1

Examiner: | **Group Art Unit: 2812**

U.S. PATENT DOCUMENTS

Examiner's Initials*		Document Number	Date MM/YYYY	Name (Family Name of First Inventor)	Class	Sub Class	Filing Date (if appropriate)
	AR						
	BR						
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FOREIGN PATENT DOCUMENTS

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							Enclosed	No	Enclose	No
	OR									
	PR									
	QR									
	RR									
	SR									
	TR									
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Examiner | Date Considered:

Atty. Dkt. No.	M#		Client Ref.		
		284032	01F171		

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Applicant: YAMADA et al.

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Examiner: Group Art Unit:

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Examiner's Initials*		Document Number	Date MM/YYYY	Name (Family Name of First Inventor)	Class	Sub Class	Filing Date (if appropriate)
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FOREIGN PATENT DOCUMENTS

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	ZR					
	AAR					

Examiner: _____   Date Considered: 11/24/04

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.